

AMENDMENTS

In The Title

Please replace the title with the following new title: --Methods Of
Forming Fluorine Doped Insulating Materials--

In the Claims

Please amend Claims 1, 18, 21, 23 and 25 as follows:

1. (Twice Amended) A method of forming [an] a fluorine
doped insulating material comprising:

providing a substrate within a reaction chamber, the reaction
chamber controlled within a range of temperatures from above [at a
temperature of from about] 400 degrees Celsius (°C) to not greater than
about 700 °C;

providing reactants comprising silicon, fluorine and ozone within the
reaction chamber; and

depositing an insulating material, at a rate of from about 1000
angstroms per minute (Å/min) to about 10000 Å/min, comprising fluorine,
silicon and oxygen onto the substrate from the reactants.

18. (Twice Amended) A method of forming a silicon oxide
having Si-F bonds, comprising:

1 providing [a substrate within] a reaction chamber at a temperature
2 in excess of [from about] 400 degrees Celsius (°C) but less than [to
3 about] ⁶³⁰700 °C;

4 positioning a substrate within the reaction chamber;

5 providing [reactants comprising] an ozone comprising reactant and
6 a precursor having Si-F bonds to the substrate within the reaction
7 chamber; and

8 causing [depositing] a silicon oxide having Si-F bonds, to deposit
9 onto the substrate within the reaction chamber at a rate of from about
10 1000 angstroms per minute (Å/min) to about 10000 Å/min[, onto the
11 substrate from the reactants].

12
13 21. (Twice Amended) A method of forming a boron-doped
14 silicon oxide having Si-F bonds, comprising:

15 providing a substrate within a reaction chamber, the reaction
16 chamber having [at] a temperature [of from about] in excess of 400
17 degrees Celsius (°C)[to about 700 °C];

18 providing reactants comprising triethoxy fluorosilane, a
19 boron-containing precursor and ozone within the reaction chamber; and

20 causing [depositing] a boron-doped silicon oxide having Si-F bonds,
21 to deposit onto the substrate at a rate of from about 1000 angstroms
22 per minute (Å/min) to about 10000 Å/min[, onto the substrate from the
23 reactants.]

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C2
BX

1 23. (Twice Amended) [A] The method of Claim 1 wherein
2 [forming a phosphorus-doped silicon oxide having Si-F bonds, comprising:
3 providing a substrate within a reaction chamber at a temperature
4 of from about 400 degrees Celsius (°C) to about 700 °C;
5]providing reactants comprising silicon, fluorine and ozone within
6 the reaction chamber comprise
7 providing reactants comprising triethoxy fluorosilane, a
8 phosphorus-containing precursor and ozone, wherein the insulating
9 material deposited is a phosphorus-doped silicon oxide material having
10 Si-F bonds, and[within the reaction chamber; and
11 depositing a phosphorus-doped silicon oxide having Si-F bonds, at
12 a rate of from about 1000 angstroms per minute (Å/min) to about 10000
13 Å/min, onto the substrate from the reactants] the depositing occurring
14 without a plasma being present in the reaction chamber.

Sub
C3

16 25. (Twice Amended) [A] The method of Claim 1 wherein
17 [forming a boron and phosphorus doped silicon oxide having Si-F bonds,
18 comprising:
19 providing a substrate within a reaction chamber at a temperature
20 of from about 400 degrees Celsius (°C) to about 700 °C;
21]providing reactants comprising silicon, fluorine and ozone within
22 the reaction chamber comprises